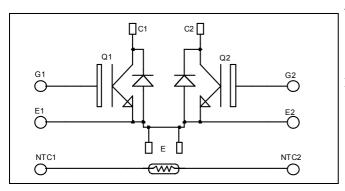


Dual common source Fast Trench + Field Stop IGBT3 Power Module

$$V_{CES} = 1200V$$

 $I_{C} = 150A$ @ $T_{C} = 80^{\circ}C$

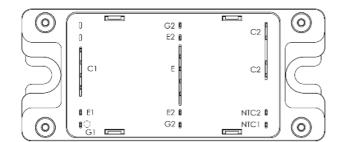


Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	220	
I_{C}	Continuous Conector Current	$T_C = 80^{\circ}C$	150	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	350	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	690	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	300A @ 1150V	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.7	2.1	V
		$I_C = 150A$ $T_j = 125^{\circ}C$		2.0		·	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		10.7		
C_{oes}	Output Capacitance	$V_{CE} = 25V$		0.56		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		0.48		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		280		
T_{r}	Rise Time	$V_{GE} = \pm 15V$		40		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$		420		
T_{f}	Fall Time	$R_{G} = 2.2\Omega$		75		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C	()	290		
T_{r}	Rise Time	$V_{GE} = \pm 15V$		45		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$		520		
$T_{\rm f}$	Fall Time	$R_G = 2.2\Omega$		90		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V V_{Bus} = 600V$ $T_j = 125^{\circ}C$		14		mJ
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$I_C = 150A$ $R_G = 2.2\Omega$ $T_j = 125^{\circ}C$		16		1117

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			250	μΑ
1KM	Wiazimum Reverse Leakage Current	VR 1200 V	$T_j = 125$ °C			500	μπ
I_{F}	DC Forward Current		$Tc = 80^{\circ}C$		150		A
V_{F}	Diode Forward Voltage	$I_{\rm F} = 150A$	$T_i = 25^{\circ}C$		1.6	2.1	V
V F	Diode Forward Voltage	1 _F 130A	$T_{i} = 125^{\circ}C$		1.6		•
t_{rr}	t _{rr} Reverse Recovery Time	$T_j = 25^{\circ}C$		170		ns	
٩r	reverse recovery Time	$T_i = 125^{\circ}C$	$T_j = 125$ °C		280		113
Q _{rr}	Reverse Recovery Charge	$\begin{split} I_F &= 150 A \\ V_R &= 600 V \\ di/dt &= 3000 A/\mu s \end{split} .$	$T_j = 25^{\circ}C$		15		μС
Vп	Reverse Recovery Charge		$T_j = 125$ °C		29		μС
E_{r}	Reverse Recovery Energy		$T_i = 25^{\circ}C$		7		mJ
\mathbf{L}_{r}	Reverse Recovery Ellergy		$T_j = 125$ °C		12		1113



 $Temperature\ sensor\ NTC\ (see\ application\ note\ APT0406\ on\ www.microsemi.com\ for\ more\ information).$

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

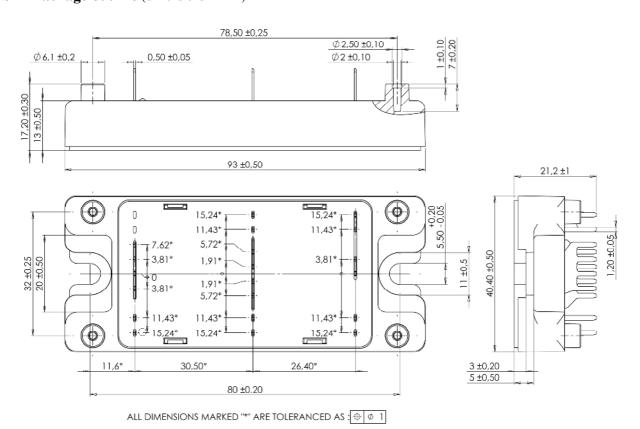
$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_{T}: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.18	°C/W
TthJC			Diode			0.34	C/ VV
V_{ISOL}	RMS Isolation Voltage, any terminal to case t	=1 min, 50/60Hz		4000			V
T_{J}	Operating junction temperature range		-40		150		
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		125	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight				160	g	

SP4 Package outline (dimensions in mm)

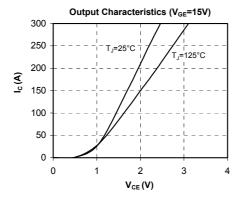


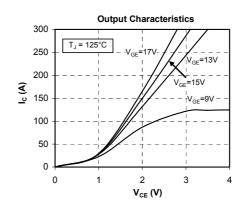
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

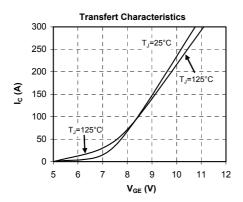
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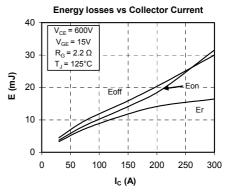


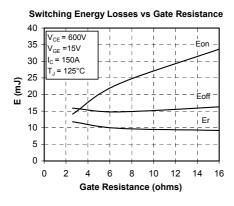
Typical Performance Curve

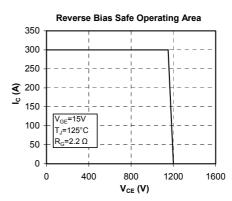


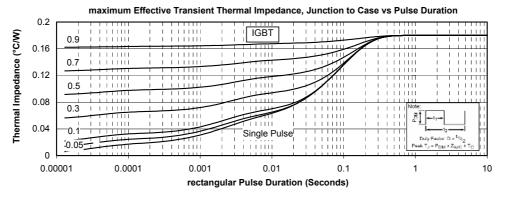




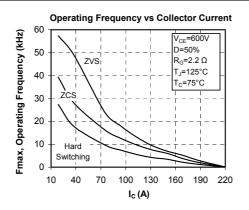


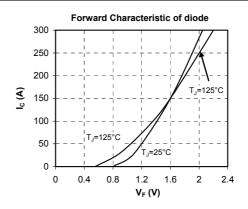


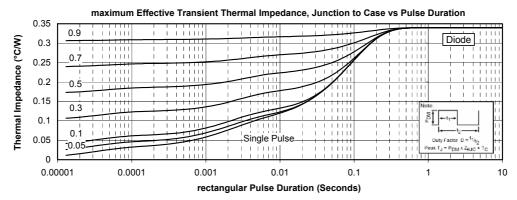












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